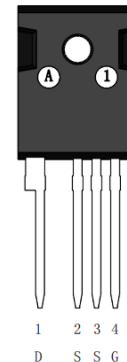


Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

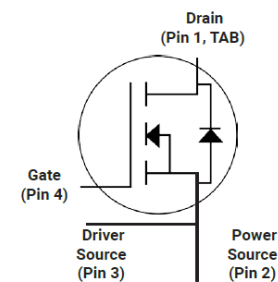
Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free



Application

- EV Charging
- DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules
- Solar PV inverters



Ordering Information

Part Number	Marking	Package	Packaging
ASC100N650MT4	ASC100N650MT4	TO247-4	Tube

Absolute Maximum Ratings($T_c=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	650	V
I_D	Drain Current(continuous)at $T_c=25^{\circ}\text{C}$	150	A
I_D	Drain Current(continuous)at $T_c=100^{\circ}\text{C}$	100	A
I_{DM}	Drain Current (pulsed)	300	A
V_{GS}	Gate-Source Voltage	-10/+22	V
P_D	Power Dissipation $T_c = 25^{\circ}\text{C}$	550	W
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$

Electrical Characteristics($T_J = 25^{\circ}\text{C}$ unless otherwise specified)
Typical Performance-Static

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	650			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650\text{V},$ $V_{GS}=0\text{V}, T_J=25^{\circ}\text{C}$			100	μA
I_{GSS}	Gate-body Leakage Current	$V_{DS}=0\text{V}; V_{GS}=-10\text{ to }20\text{V}$			250	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=22\text{mA}$	2	3	4	V
$V_{GS(on)}$	Recommended turn-on Voltage	Static		18		V
$V_{GS(off)}$	Recommended turn-off Voltage			-5		V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS}=18\text{V}, I_D=75\text{A}$		12	15	m Ω
		$V_{GS}=18\text{V}, I_D=75\text{A}$ $T_J=175^{\circ}\text{C}$		16		m Ω

Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=400V, f=1MHz,$ $V_{AC}=25mV$		7169		pF
C_{oss}	Output Capacitance			325		pF
C_{rss}	Reverse Transfer Capacitance			31		pF
g_{fs}	Transconductance	$V_{DS}=20V, I_D=15A$		42		S
E_{OSS}	C_{OSS} Stored Energy	$V_{DS}=400V, f=1MHz$		32		μJ
E_{ON}	Turn-On Energy (Body Diode)	$V_{DS}=400V, V_{GS}=-5/20V,$ $I_D=50A, L=60\mu H$ $T_J=175^\circ C$		436		μJ
E_{OFF}	Turn-Off Energy (Body Diode)			287		μJ
Q_g	Total Gate Charge	$V_{DS}=400V, V_{GS}=-5V/20V,$ $I_D=50A$		236		nC
Q_{gs}	Gate-source Charge			56		nC
Q_{gd}	Gate-Drain Charge			64		nC
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		2.2		Ω
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=400V, V_{GS}=-5V/20V,$ $I_D=50A, L=60\mu H$ $R_{ext}=5\Omega$		26		ns
t_r	Rise Time			35		ns
$t_{d(off)}$	Turn-off Delay Time			63		ns
t_f	Fall Time			17		ns

Typical Performance-Reverse Diode($T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FSD}	Forward Voltage	$V_{GS}=0V, I_F=50A, T_J=25^\circ C$		3.5	6	V
		$V_{GS}=0V, I_F=50A, T_J=175^\circ C$		3.0	6	V
I_S	Continuous Diode Forward Current	$V_{GS}=0V, T_C=25^\circ C$		80		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-5V, I_F=50A,$ $V_R=400V, T_J=175^\circ C$ $di/dt=2400A/\mu s$		88		nS
Q_{rr}	Reverse Recovery Charge			680		nC
I_{rrm}	Peak Reverse Recovery Current			17		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.27	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^\circ C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of $T_J(max)=175^\circ C$

Electrical Characteristics

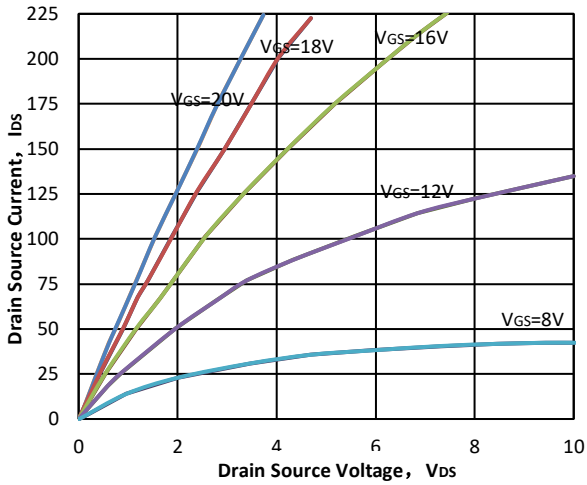
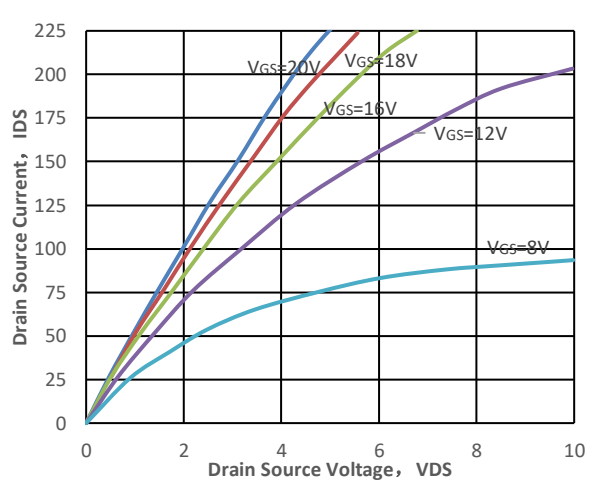
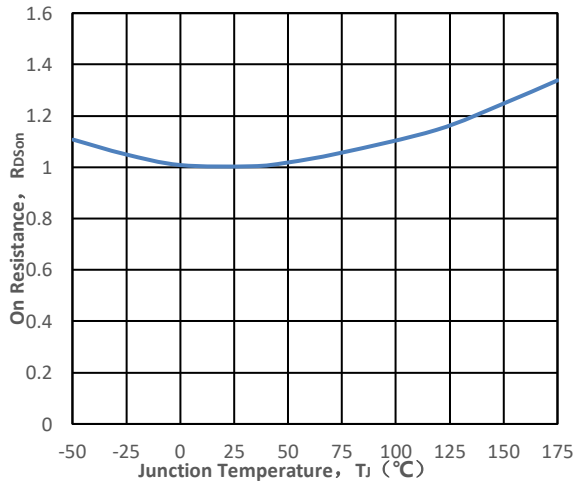
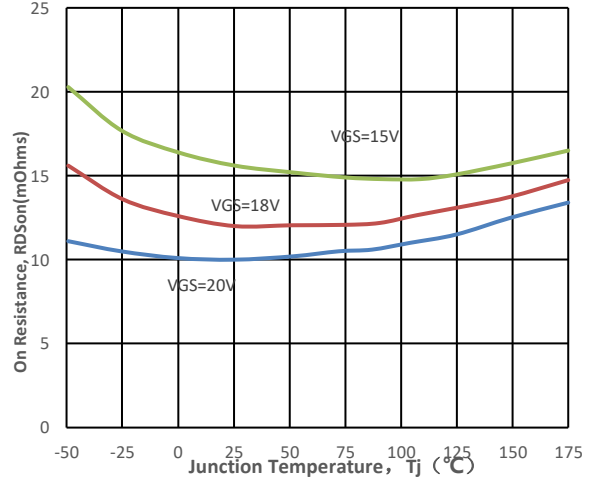
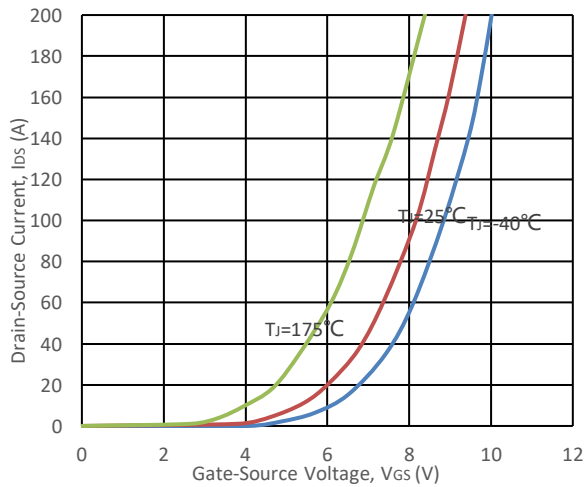
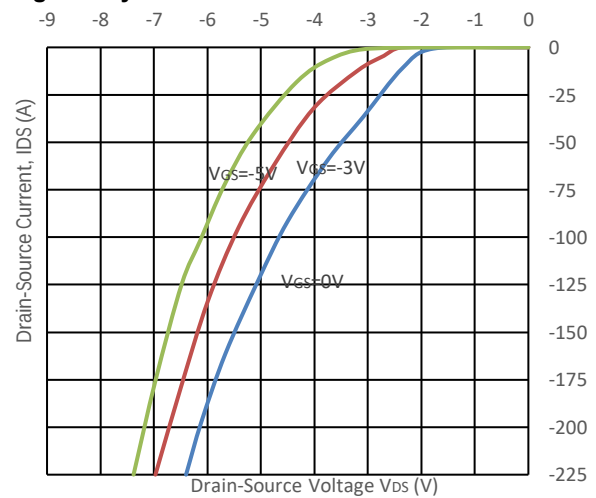
Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

Fig2. Output characteristics ($T_J = 175^\circ\text{C}$)

Fig3. Normalized On-Resistance vs. Temperature

Fig4. On-Resistance vs. Temperature

Fig5. Transfer Characteristic

Fig6. Body Diode Characteristic at 25°C


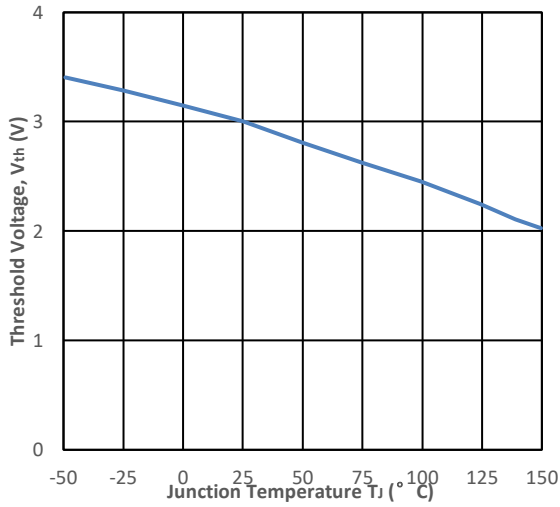
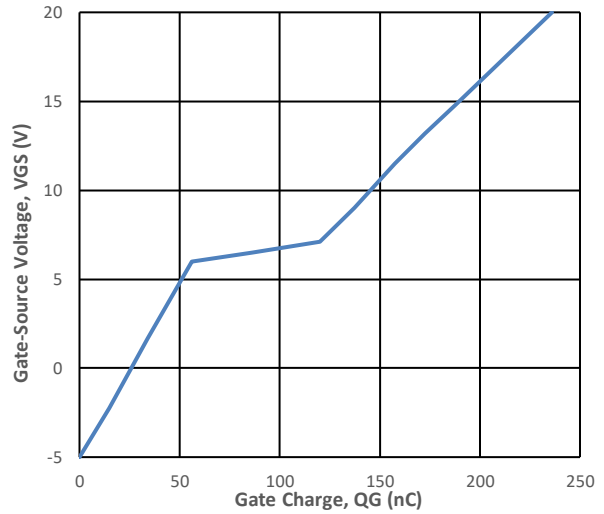
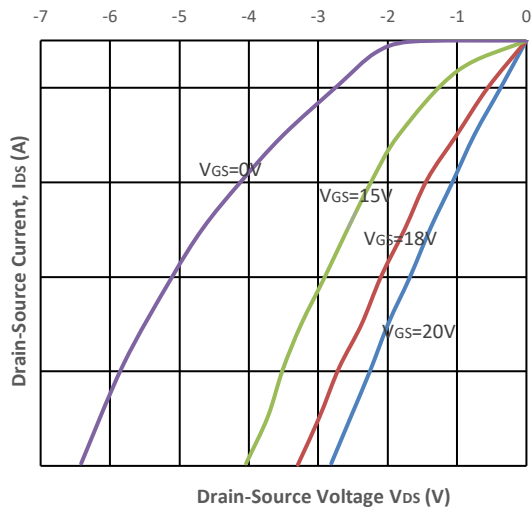
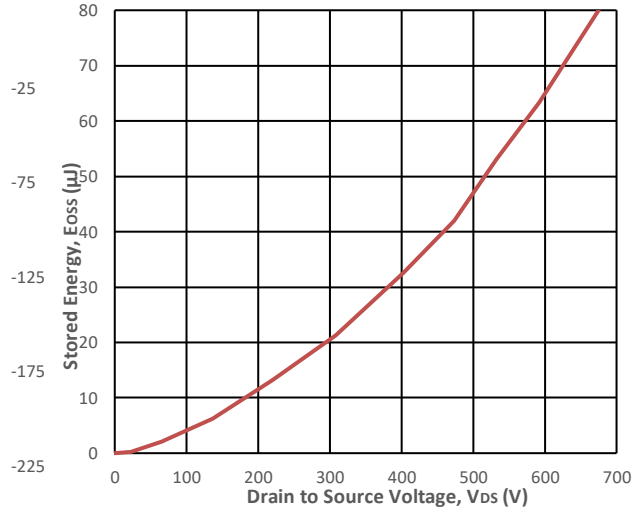
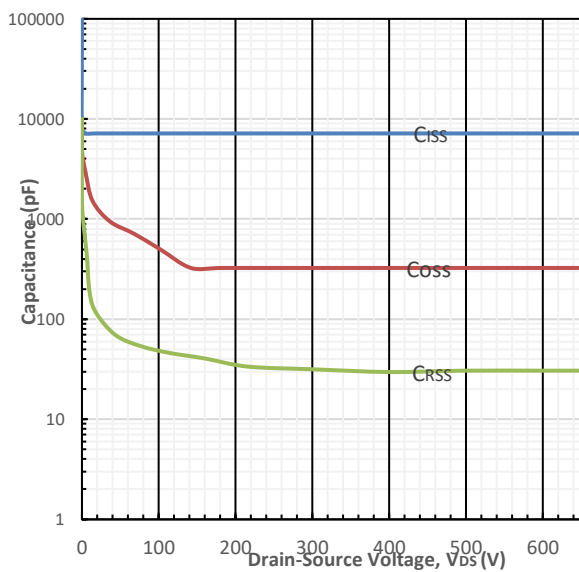
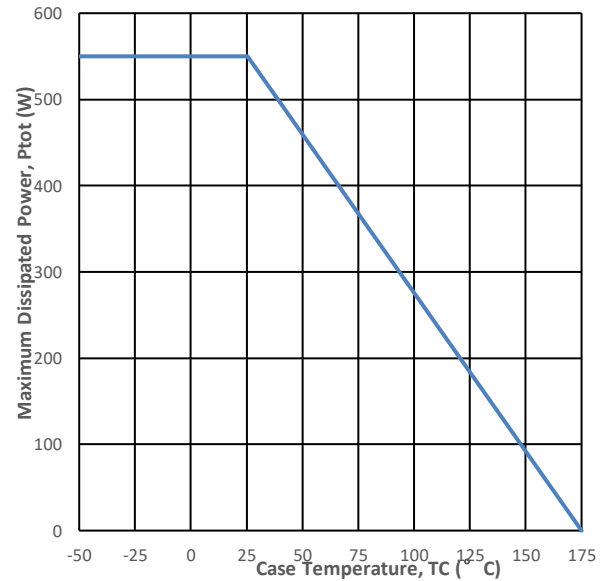
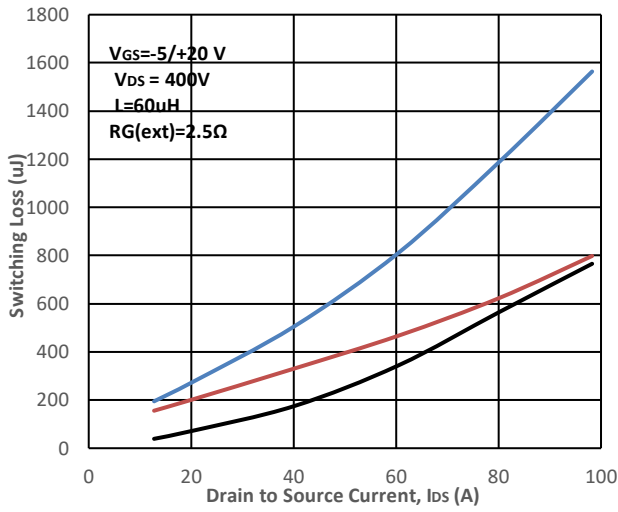
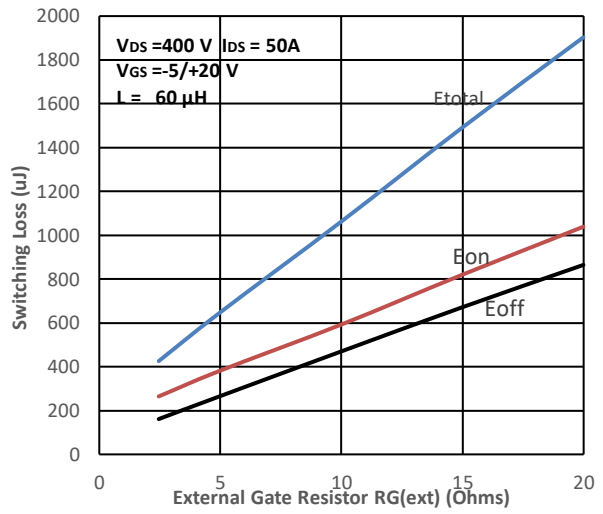
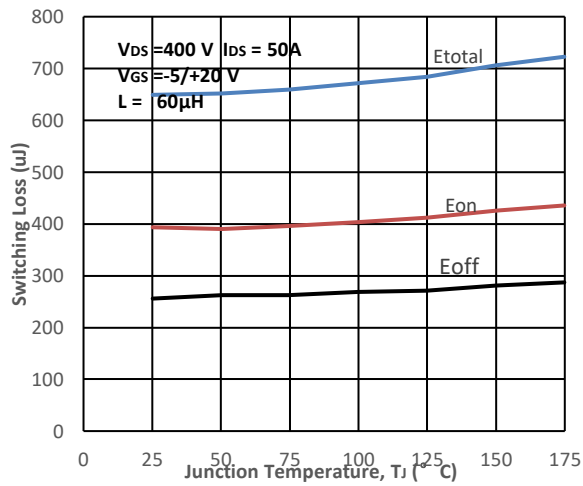
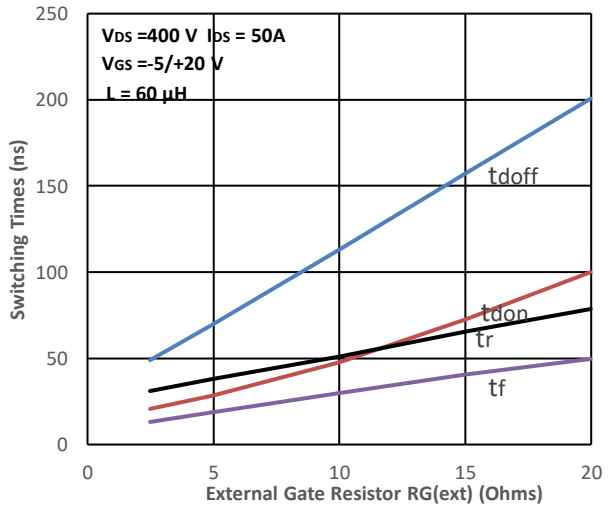
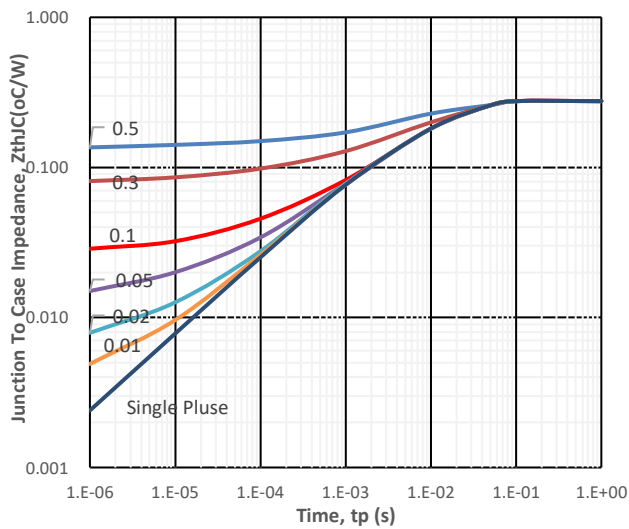
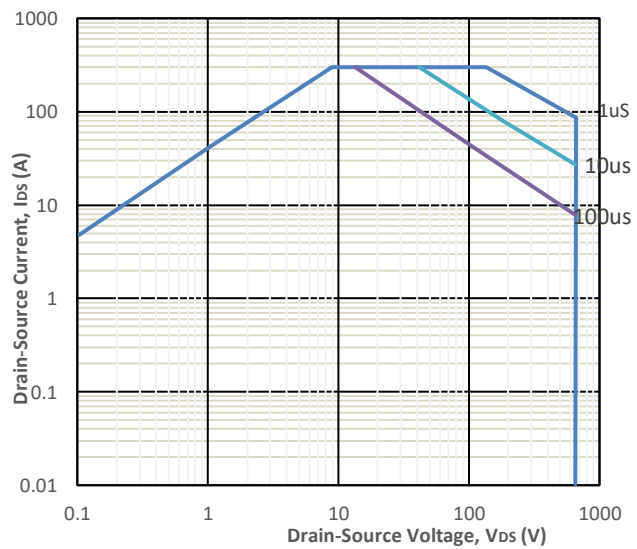
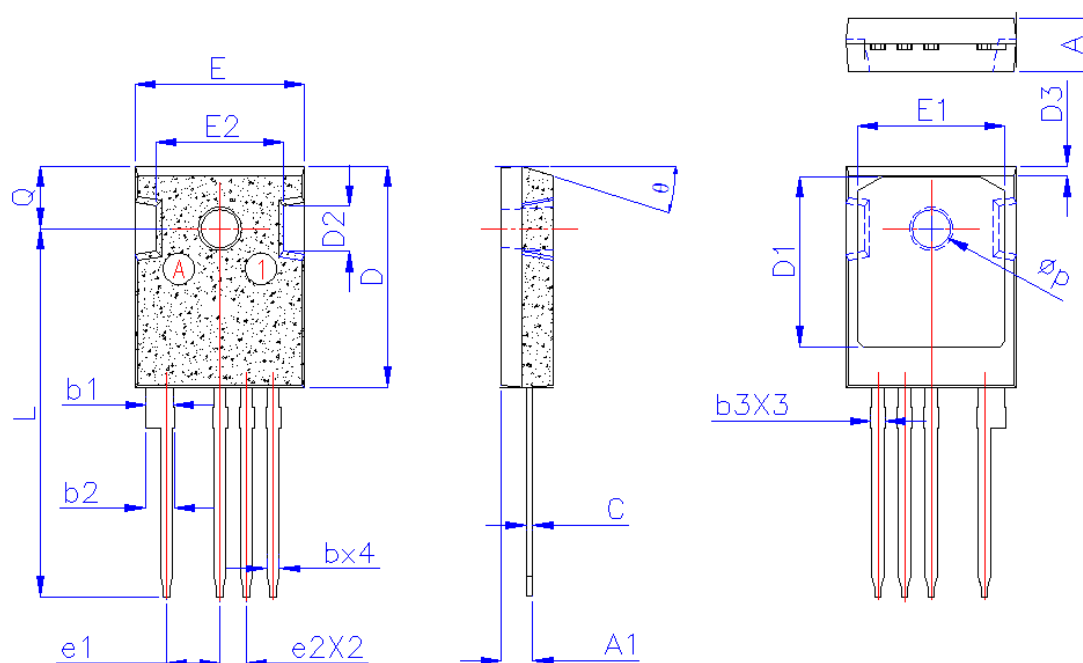
Fig7. Threshold Voltage vs. Temperature

Fig8. Gate Charge Characteristics

Fig9. 3rd Quadrant Characteristic at 25 $^{\circ}$ C

Fig10. Output Capacitor Stored Energy

Fig11. Capacitances vs. Drain-Source

Fig12. Max Power Dissipation Derating Vs T_c


Fig13. Switching Energy vs. Drain Current

Fig14. Switching Energy vs. $R_{G(ext)}$

Fig15. Switching Energy vs. Temperature

Fig16. Switching Times vs. $R_{G(ext)}$

Fig17. Transient Thermal Impedance

Fig18. Safe Operating Area


Package Drawing:

Dimensions (UNIT: mm)

SYMBDLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	TYPE	MAX	MIN	TYPE	MAX
A	4.80	5.00	5.20	0.189	0.197	0.205
A1	2.85	3.00	3.15	0.112	0.118	0.124
b	1.15	1.20	1.25	0.045	0.047	0.049
b1	2.40	2.50	2.60	0.094	0.098	0.102
b2	2.61	2.76	2.91	0.103	0.109	0.115
b3	1.30	1.42	1.57	0.051	0.056	0.062
C	0.55	0.60	0.65	0.022	0.024	0.026
D	20.80	21.00	21.20	0.819	0.827	0.835
D1	15.94	16.24	16.54	0.628	0.639	0.651
D2	4.3 TYPE			0.169 TYPE		
e1	4.93	5.08	5.23	0.194	0.200	0.206
e2	2.39	2.54	2.69	0.094	0.100	0.106
E	15.95	16.15	16.35	0.628	0.636	0.644
E1	13.82	14.02	14.26	0.544	0.552	0.561
E2	12.00	12.20	12.40	0.472	0.480	0.488
L	34.65	35.05	35.45	1.364	1.380	1.396
Q	5.85	5.95	6.05	0.230	0.234	0.238
øP	3.45	3.60	3.75	0.136	0.142	0.148
θ	17.5°			0.689°		

Notes:

- The information in this document is subject to change without notice.
- For more product and company information, please contact us or visit the website.
- ©2023 Shenzhen AST Technology Company. All Rights Reserved.

Contact Info:

- Tel: +86 755-89300160
- Web: www.astsic.com
- Add: No.1 Rongtian Rd., Kendzi Street, Pingshan District, Shenzhen, China

Offical Account:



专注

Focus

品质

Quality

创新

Innovation

共赢

Win-win

